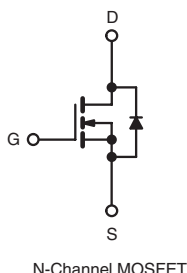
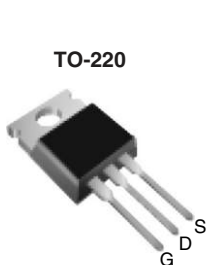


**Power MOSFET****PRODUCT SUMMARY**

|                           |                        |       |
|---------------------------|------------------------|-------|
| $V_{DS}$ (V)              | 500                    |       |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10\text{ V}$ | 0.450 |
| $Q_g$ (Max.) (nC)         | 81                     |       |
| $Q_{gs}$ (nC)             | 20                     |       |
| $Q_{gd}$ (nC)             | 36                     |       |
| Configuration             | Single                 |       |



N-Channel MOSFET

**FEATURES**

- Lower Gate Charge  $Q_g$  Results in Simpler Drive Requirements
- Improved Gate, Avalanche and Dynamic  $dV/dt$  Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage
- Lead (Pb)-free Available

**RoHS\***  
COMPLIANT**APPLICATIONS**

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supplies
- High Speed Power Switching

**ORDERING INFORMATION**

|                |                |
|----------------|----------------|
| Package        | TO-220         |
| Lead (Pb)-free | IRFB13N50APbF  |
|                | SiHFB13N50A-E3 |
| SnPb           | IRFB13N50A     |
|                | SiHFB13N50A    |

**ABSOLUTE MAXIMUM RATINGS**  $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted

| PARAMETER                                        |                         |                         | SYMBOL                            | LIMIT            | UNIT  |
|--------------------------------------------------|-------------------------|-------------------------|-----------------------------------|------------------|-------|
| Drain-Source Voltage                             |                         |                         | V <sub>DS</sub>                   | 500              | V     |
| Gate-Source Voltage                              |                         |                         | V <sub>GS</sub>                   | ± 30             |       |
| Continuous Drain Current                         | V <sub>GS</sub> at 10 V | T <sub>C</sub> = 25 °C  | I <sub>D</sub>                    | 14               | A     |
|                                                  |                         | T <sub>C</sub> = 100 °C |                                   | 9.1              |       |
| Pulsed Drain Current <sup>a</sup>                |                         |                         | I <sub>DM</sub>                   | 56               |       |
| Linear Derating Factor                           |                         |                         |                                   | 2.0              | W/°C  |
| Single Pulse Avalanche Energy <sup>b</sup>       |                         |                         | E <sub>AS</sub>                   | 560              | mJ    |
| Avalanche Current <sup>a</sup>                   |                         |                         | I <sub>AR</sub>                   | 14               | A     |
| Repetitive Avalanche Energy <sup>a</sup>         |                         |                         | E <sub>AR</sub>                   | 25               | mJ    |
| Maximum Power Dissipation                        | T <sub>C</sub> = 25 °C  |                         | P <sub>D</sub>                    | 250              | W     |
| Peak Diode Recovery dV/dt <sup>c</sup>           |                         |                         | dV/dt                             | 9.2              | V/ns  |
| Operating Junction and Storage Temperature Range |                         |                         | T <sub>J</sub> , T <sub>stg</sub> | - 55 to + 150    | °C    |
| Soldering Recommendations (Peak Temperature)     | for 10 s                |                         |                                   | 300 <sup>d</sup> |       |
| Mounting Torque                                  | 6-32 or M3 screw        |                         |                                   | 10               |       |
|                                                  |                         |                         |                                   | 1.1              | N · m |

**Notes**

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 5.7\text{ mH}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AS} = 14\text{ A}$ ,  $dV/dt = 7.6\text{ V/ns}$  (see fig. 12a).
- $I_{SD} \leq 14\text{ A}$ ,  $dI/dt \leq 250\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

**THERMAL RESISTANCE RATINGS**

| PARAMETER                           | SYMBOL     | TYP. | MAX. | UNIT |
|-------------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient         | $R_{thJA}$ | -    | 62   | °C/W |
| Case-to-Sink, Flat, Greased Surface | $R_{thCS}$ | 0.50 | -    |      |
| Maximum Junction-to-Case (Drain)    | $R_{thJC}$ | -    | 0.50 |      |

**SPECIFICATIONS**  $T_J = 25\text{ °C}$ , unless otherwise noted

| PARAMETER                                 | SYMBOL                           | TEST CONDITIONS                                                                                                                                         |                                                                                                        | MIN. | TYP. | MAX.  | UNIT |
|-------------------------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------|------|------|-------|------|
| Static                                    |                                  |                                                                                                                                                         |                                                                                                        |      |      |       |      |
| Drain-Source Breakdown Voltage            | V <sub>DS</sub>                  | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                                                          |                                                                                                        | 500  | -    | -     | V    |
| V <sub>DS</sub> Temperature Coefficient   | ΔV <sub>DS</sub> /T <sub>J</sub> | Reference to 25 °C, I <sub>D</sub> = 1 mA                                                                                                               |                                                                                                        | -    | 0.55 | -     | V/°C |
| Gate-Source Threshold Voltage             | V <sub>GS(th)</sub>              | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                                                             |                                                                                                        | 2.0  | -    | 4.0   | V    |
| Gate-Source Leakage                       | I <sub>GSS</sub>                 | V <sub>GS</sub> = ± 30 V                                                                                                                                |                                                                                                        | -    | -    | ± 100 | nA   |
| Zero Gate Voltage Drain Current           | I <sub>DSS</sub>                 | V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V                                                                                                          |                                                                                                        | -    | -    | 25    | μA   |
|                                           |                                  | V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C                                                                                 |                                                                                                        | -    | -    | 250   |      |
| Drain-Source On-State Resistance          | R <sub>DS(on)</sub>              | V <sub>GS</sub> = 10 V                                                                                                                                  | I <sub>D</sub> = 8.4 A <sup>b</sup>                                                                    | -    | -    | 0.450 | Ω    |
| Forward Transconductance                  | g <sub>fs</sub>                  | V <sub>DS</sub> = 50 V, I <sub>D</sub> = 8.4 A                                                                                                          |                                                                                                        | 8.1  | -    | -     | S    |
| Dynamic                                   |                                  |                                                                                                                                                         |                                                                                                        |      |      |       |      |
| Input Capacitance                         | C <sub>iss</sub>                 | V <sub>GS</sub> = 0 V,<br>V <sub>DS</sub> = 25 V,<br>f = 1.0 MHz, see fig. 5                                                                            |                                                                                                        | -    | 1910 | -     | pF   |
| Output Capacitance                        | C <sub>oss</sub>                 |                                                                                                                                                         |                                                                                                        | -    | 290  | -     |      |
| Reverse Transfer Capacitance              | C <sub>rss</sub>                 |                                                                                                                                                         |                                                                                                        | -    | 11   | -     |      |
| Output Capacitance                        | C <sub>oss</sub>                 | V <sub>GS</sub> = 0 V                                                                                                                                   | V <sub>DS</sub> = 1.0 V, f = 1.0 MHz                                                                   | -    | 2730 | -     |      |
|                                           |                                  |                                                                                                                                                         | V <sub>DS</sub> = 400 V, f = 1.0 MHz                                                                   | -    | 82   | -     |      |
| Effective Output Capacitance              | C <sub>oss eff.</sub>            | V <sub>DS</sub> = 0 V to 400 V <sup>c</sup>                                                                                                             |                                                                                                        | -    | 160  | -     |      |
| Total Gate Charge                         | Q <sub>g</sub>                   | V <sub>GS</sub> = 10 V                                                                                                                                  | I <sub>D</sub> = 14 A, V <sub>DS</sub> = 400 V,<br>see fig. 6 and 13 <sup>b</sup>                      | -    | -    | 81    | nC   |
| Gate-Source Charge                        | Q <sub>gs</sub>                  |                                                                                                                                                         |                                                                                                        | -    | -    | 20    |      |
| Gate-Drain Charge                         | Q <sub>gd</sub>                  |                                                                                                                                                         |                                                                                                        | -    | -    | 36    |      |
| Turn-On Delay Time                        | t <sub>d(on)</sub>               |                                                                                                                                                         | V <sub>DD</sub> = 250 V, I <sub>D</sub> = 14 A,<br>R <sub>G</sub> = 7.5 Ω,<br>see fig. 10 <sup>b</sup> | -    | 15   | -     | ns   |
| Rise Time                                 | t <sub>r</sub>                   |                                                                                                                                                         |                                                                                                        | -    | 39   | -     |      |
| Turn-Off Delay Time                       | t <sub>d(off)</sub>              |                                                                                                                                                         |                                                                                                        | -    | 39   | -     |      |
| Fall Time                                 | t <sub>f</sub>                   |                                                                                                                                                         |                                                                                                        | -    | 31   | -     |      |
| Drain-Source Body Diode Characteristics   |                                  |                                                                                                                                                         |                                                                                                        |      |      |       |      |
| Continuous Source-Drain Diode Current     | I <sub>S</sub>                   | MOSFET symbol showing the integral reverse p - n junction diode<br> |                                                                                                        | -    | -    | 14    | A    |
| Pulsed Diode Forward Current <sup>a</sup> | I <sub>SM</sub>                  |                                                                                                                                                         |                                                                                                        | -    | -    | 56    |      |
| Body Diode Voltage                        | V <sub>SD</sub>                  | T <sub>J</sub> = 25 °C, I <sub>S</sub> = 14 A, V <sub>GS</sub> = 0 V <sup>b</sup>                                                                       |                                                                                                        | -    | -    | 1.5   | V    |
| Body Diode Reverse Recovery Time          | t <sub>rr</sub>                  | T <sub>J</sub> = 25 °C, I <sub>F</sub> = 14 A,<br>T <sub>J</sub> = 125 °C, dI/dt = 100 A/μs <sup>b</sup>                                                |                                                                                                        | -    | 370  | 550   | ns   |
| Body Diode Reverse Recovery Charge        | Q <sub>rr</sub>                  |                                                                                                                                                         |                                                                                                        | -    | 4.4  | 6.5   | μC   |
| Body Diode Reverse Recovery Current       | I <sub>RRM</sub>                 |                                                                                                                                                         |                                                                                                        | -    | 21   | 31    | A    |
| Forward Turn-On Time                      | t <sub>on</sub>                  | Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )                                                       |                                                                                                        |      |      |       |      |

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .  
c.  $C_{oss\text{ eff.}}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80 %  $V_{DS}$ .

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

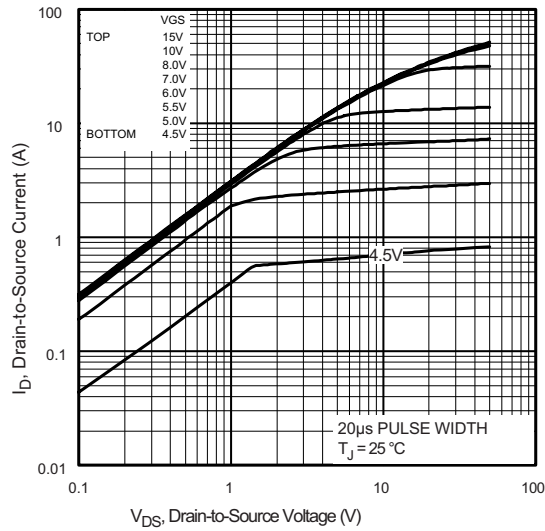


Fig. 1 - Typical Output Characteristics

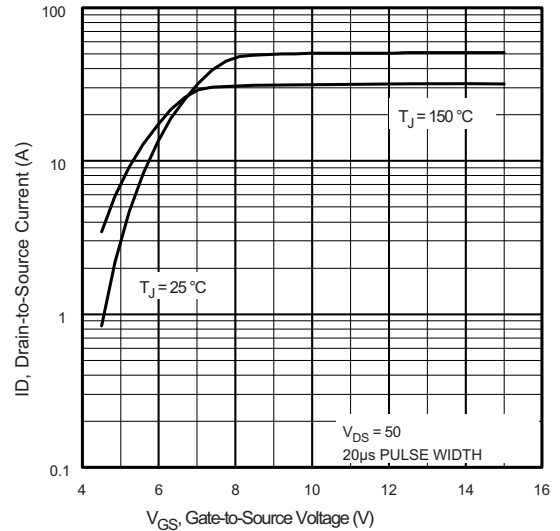


Fig. 3 - Typical Transfer Characteristics

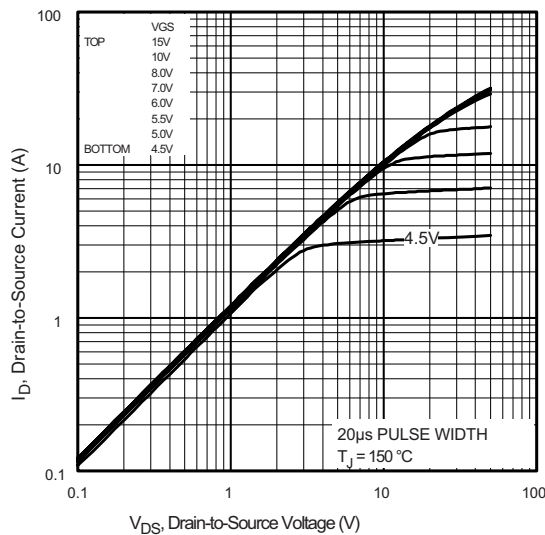


Fig. 2 - Typical Output Characteristics

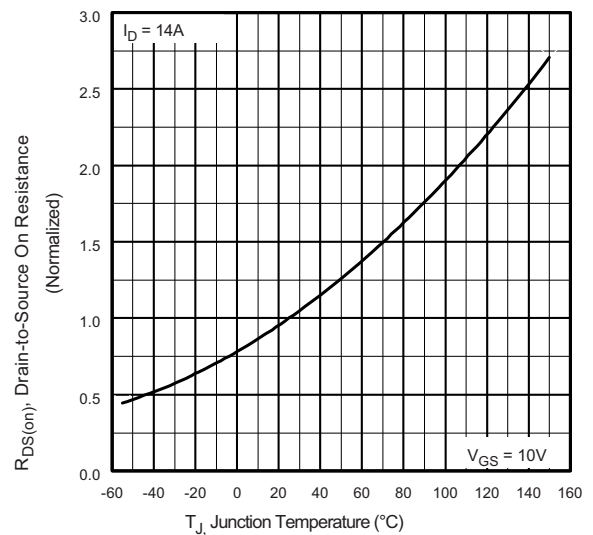


Fig. 4 - Normalized On-Resistance vs. Temperature

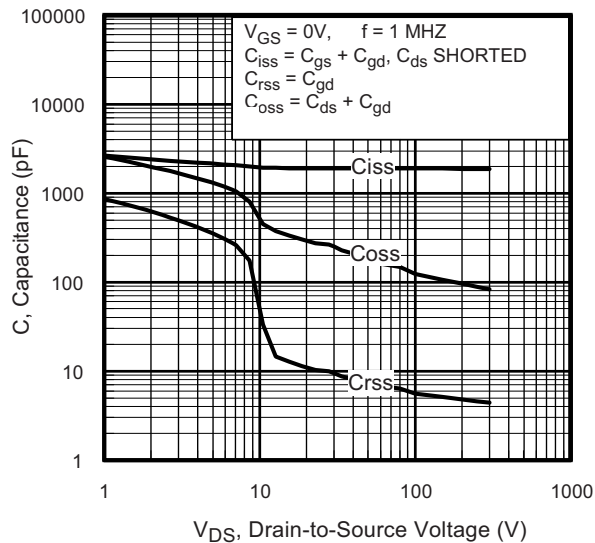


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

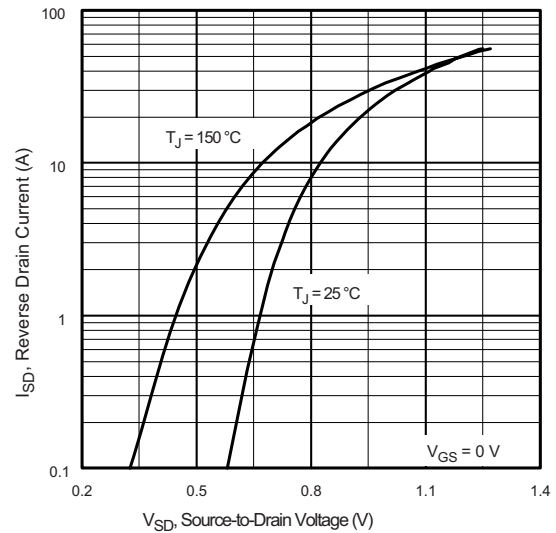


Fig. 7 - Typical Source-Drain Diode Forward Voltage

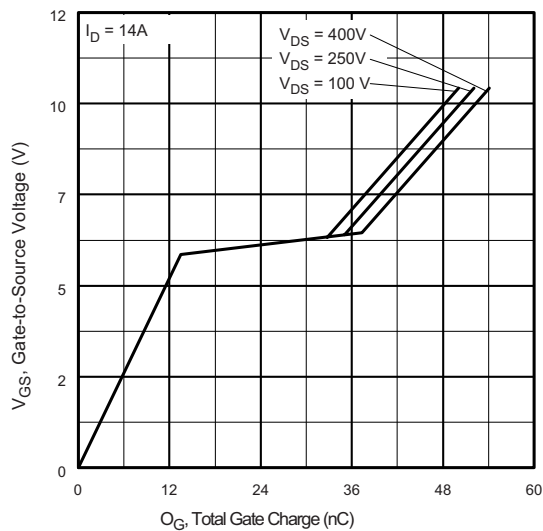


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

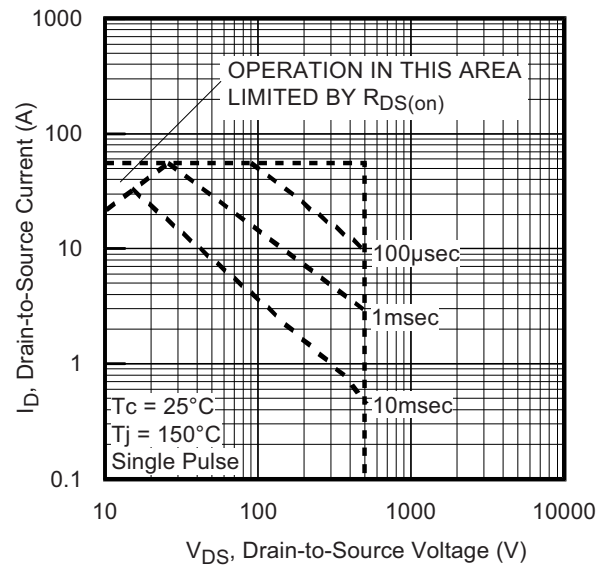


Fig. 8 - Maximum Safe Operating Area

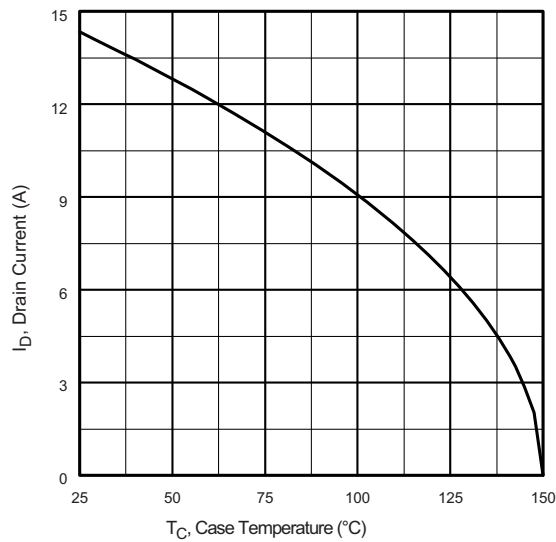


Fig. 9 - Maximum Drain Current vs. Case Temperature

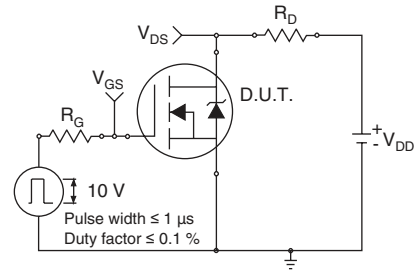


Fig. 10a - Switching Time Test Circuit

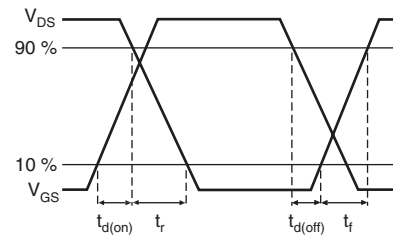


Fig. 10b - Switching Time Waveforms

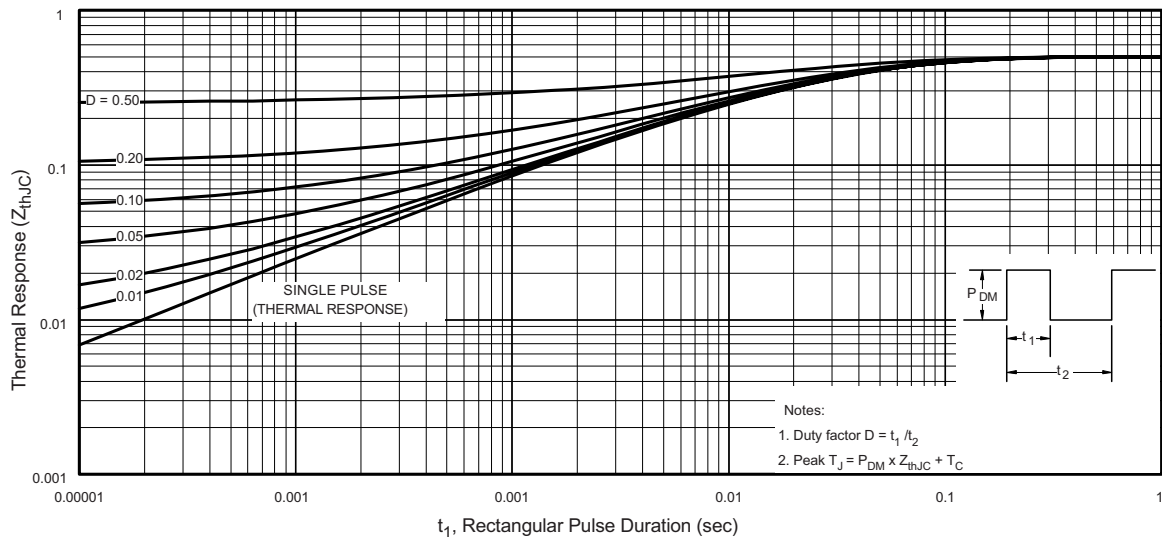


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

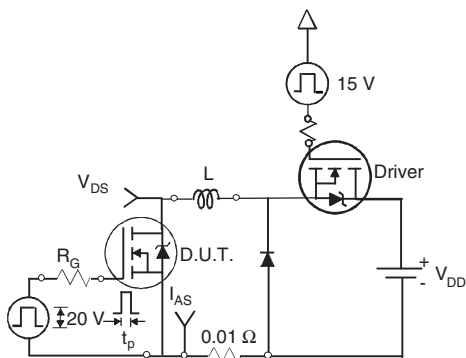


Fig. 12a - Unclamped Inductive Test Circuit

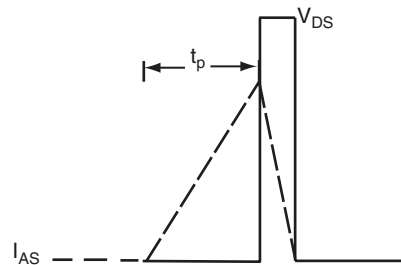


Fig. 12b - Unclamped Inductive Waveforms

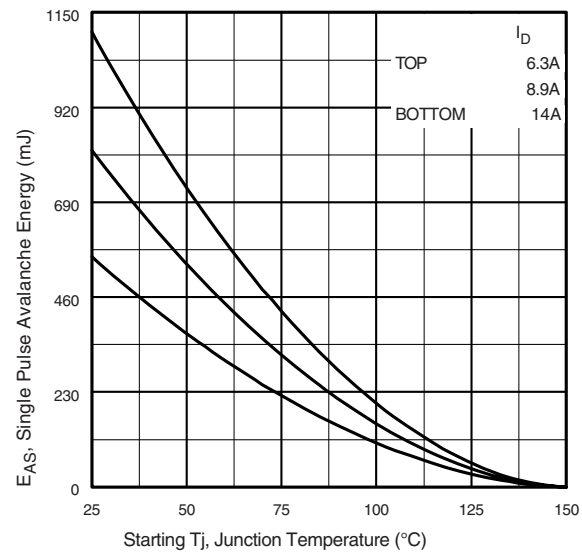


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

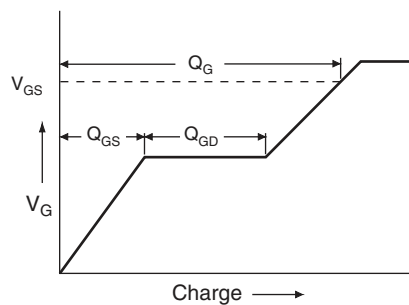


Fig. 13a - Basic Gate Charge Waveform

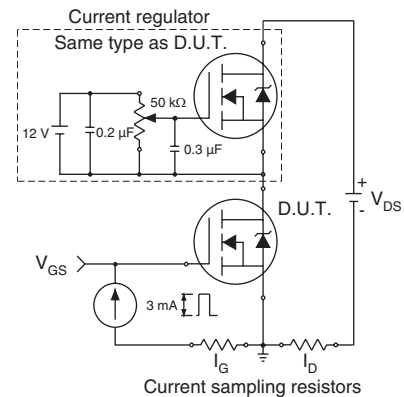
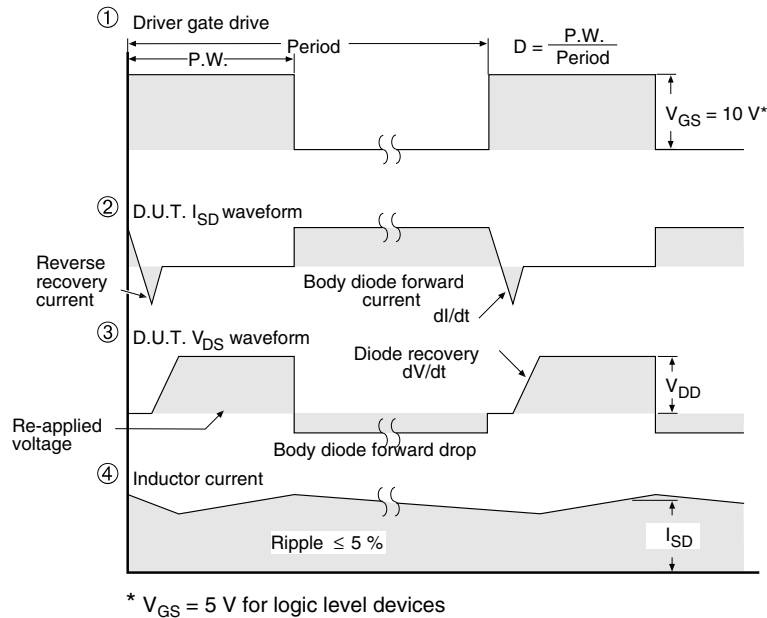
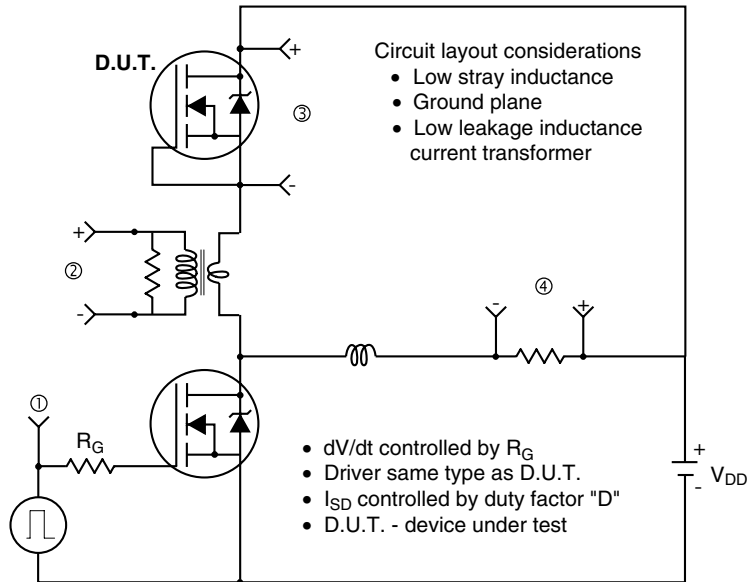


Fig. 13b - Gate Charge Test Circuit

## Peak Diode Recovery $dV/dt$ Test Circuit



**Fig. 14 - For N-Channel**

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